

# Yuji Yamamoto

## List of Publications by Year in descending order

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docs citations

25  
times ranked

390  
citing authors

#	ARTICLE	IF	CITATIONS
1	Low threading dislocation density Ge deposited on Si (100) using RPCVD. Solid-State Electronics, 2011, 60, 2-6.	1.4	114
2	Low threading dislocation Ge on Si by combining deposition and etching. Thin Solid Films, 2012, 520, 3216-3221.	1.8	37
3	CMOS-Compatible Bias-Tunable Dual-Band Detector Based on GeSn/Ge/Si Coupled Photodiodes. ACS Photonics, 2021, 8, 2166-2173.	6.6	36
4	Atomic layer processing for doping of SiGe. Thin Solid Films, 2006, 508, 279-283.	1.8	27
5	Reduction of threading dislocation density beyond the saturation limit by optimized reverse grading. Physical Review Materials, 2020, 4, .	2.4	20
6	Base doping and dopant profile control of SiGe npn and pnp HBTs. Applied Surface Science, 2008, 254, 6013-6016.	6.1	19
7	The impact of donors on recombination mechanisms in heavily doped Ge/Si layers. Journal of Applied Physics, 2017, 121, 245701.	2.5	19
8	Influence of annealing conditions on threading dislocation density in Ge deposited on Si by reduced pressure chemical vapor deposition. Semiconductor Science and Technology, 2018, 33, 124007.	2.0	19
9	B atomic layer doping of Ge. Thin Solid Films, 2010, 518, S44-S47.	1.8	15
10	Phosphorus atomic layer doping in Ge using RPCVD. Solid-State Electronics, 2013, 83, 25-29.	1.4	14
11	Synthesis of Armchair Graphene Nanoribbons on Germanium-on-Silicon. Journal of Physical Chemistry C, 2019, 123, 18445-18454.	3.1	12
12	A self-ordered, body-centered tetragonal superlattice of SiGe nanodot growth by reduced pressure CVD. Nanotechnology, 2017, 28, 485303.	2.6	10
13	Photoluminescence from GeSn nano-heterostructures. Nanotechnology, 2018, 29, 415702.	2.6	9
14	Arsenic atomic layer doping in Si using AsH <sub>3</sub> . Solid-State Electronics, 2015, 110, 29-34.	1.4	7
15	Alignment control of self-ordered three dimensional SiGe nanodots. Semiconductor Science and Technology, 2018, 33, 114014.	2.0	5
16	Self-Ordered Ge Nanodot Fabrication by Using Reduced Pressure Chemical Vapor Deposition. ECS Journal of Solid State Science and Technology, 2019, 8, P190-P195.	1.8	4
17	Selective Polycrystalline Si and SiGe Deposition on Epitaxial Si Induced by B-Atomic Layer Doping. ECS Transactions, 2009, 16, 503-510.	0.5	3
18	Threading Dislocation Reduction of Ge by Introducing a SiGe/Ge Superlattice. ECS Journal of Solid State Science and Technology, 2021, 10, 034005.	1.8	3

#	ARTICLE	IF	CITATIONS
19	Threading Dislocation Reduction of Ge by Introducing a SiGe/Ge Superlattice. ECS Transactions, 2020, 98, 185-194.	0.5	3
20	CVD Synthesis of Armchair Graphene Nanoribbons on Ge/Si(001). ECS Transactions, 2019, 93, 133-136.	0.5	2
21	Process Effects on the Noise Performance of SiGe/Si Multi Quantum Well Thermistor. ECS Transactions, 2019, 93, 105-108.	0.5	1
22	Influence of Annealing Condition on Threading Dislocation Density of Ge Grown by RPCVD. ECS Transactions, 2019, 93, 87-90.	0.5	1
23	Threading Dislocation Reduction of Ge by Introducing a SiGe/Ge Superlattice. ECS Meeting Abstracts, 2020, MA2020-02, 1763-1763.	0.0	1
24	C and Si delta doping in Ge by CH <sub>3</sub> SiH <sub>3</sub> using reduced pressure chemical vapor deposition. Thin Solid Films, 2016, 602, 24-28.	1.8	0
25	Group IV Heteroepitaxy for Advanced Electronic Devices Integrated in BiCMOS Technology. ECS Transactions, 2019, 93, 1-5.	0.5	0